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Advanced Etch Technology and Process Integration for Nanopatterning X

**Julie Bannister
Nihar Mohanty**
Editors

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Contents

MATERIALS AND ETCH INTEGRATION

- 11615 07 **Novel bottom-up organic mandrel growth to enable organic mandrel EUV SADP for sub-5nm node technologies** [11615-5]

ADVANCED PATTERNING INTEGRATION

- 11615 0A **Contact local CD uniformity optimization through etch shrink** [11615-9]
- 11615 0B **Advanced multiple patterning technologies for high density hexagonal hole arrays** [11615-10]

ATOMIC LAYER ETCHING AND NOVEL PLASMA TECHNIQUES

- 11615 0D **Atomic level control of pattern fidelity during SAC etch (Invited Paper)** [11615-12]

PATTERNING SOLUTIONS FOR EMERGING APPLICATIONS

- 11615 0G **Effect of surface temperature on GeSbTe damage formation during plasma processing** [11615-16]

COMPUTATIONAL PATTERNING AND PATTERNING PROCESS CONTROL

- 11615 0J **Process trace analytics for process development (Invited Paper)** [11615-20]
- 11615 0K **Parametric modeling of patterned object with variations and expert tuning of edge placement** [11615-21]
- 11615 0L **Fast etch recipe creation with automated model-based process optimization** [11615-22]
- 11615 0M **EPE variability comparison study of multiple patterning options for restricted 2D structures in advanced logic nodes** [11615-23]

POSTER SESSION

- 11615 0N **On-product overlay characterization after stressed layer etch** [11615-24]